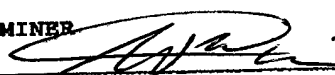


Sheet <u>1</u> of <u>1</u> FIFTH LIST OF REFERENCES CITED BY APPLICANT (REVISED FORM PTO-1449) DATED: December 27, 2002										Atty. Docket No. 3905		Serial No.: 09/519,408	
										Applicant: Takao NAKAMURA et al.			
										U.S. Filing Date: March 3, 2000 CPA FILED: 03/18/02		Art Unit: 2814	
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*EXAMINER INITIAL		DOCUMENT NO.				DATE	NAME	Cl.	Sub- Cl.	Fil. Date			
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		DOCUMENT NO.				DATE	COUNTRY	Cl.	Sub- Cl.	Trans.			
										Yes	No		
WBL	AD2	11	1	1	9	2	3	8	04/1999	Japan	-	-	Computer Translation + Abstract
OTHER DOCUMENTS													
EXAMINER 								DATE CONSIDERED <u>1/24/03</u>					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.													

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Sheet 1 of 2Atty. Docket
No. 3905Serial No.:
09/519,408**FOURTH
LIST OF REFERENCES CITED BY
APPLICANT**

(REVISED FORM PTO-1449)

DATED: June 18, 2002

Applicant: Takao NAKAMURA et al.

U.S. Filing Date:
March 3, 2000
CPA FILED: 03/18/02Art Unit:
2811

U. S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	Cl.	Sub- Cl.	File Date
				-	-	-

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.	DATE	COUNTRY	Cl.	Sub- Cl.	Trans.	
							Yes	No
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	AF	57- 1 0 6 2 4 6	06/1982	Japan <i>Utility Model</i>	-	-	x-Par. Trans.	
	AG	58 1 6 2 0 7 6	09/1983	Japan	-	-	x-Abstract	
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	AP	10 2 0 0 1 6 3	07/1998	Japan	-	-	x-Abstract	
	AQ	10 3 0 8 5 3 4	11/1998	Japan	-	-	x-Abstract	
	AR	11 0 8 7 7 7 2	03/1999	Japan	-	-	x-Abstract	
	AS	11 1 2 1 8 0 4	04/1999	Japan	-	-	x-Abstract	
	AT	2000 1 9 6 1 5 2	07/2000	Japan	-	-	x-Abstract	

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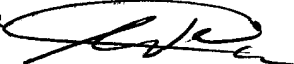
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Sheet 2 of 2 LIST OF REFERENCES CITED BY APPLICANT (REVISED FORM PTO-1449) DATED: June 18, 2002				Atty. Docket No. 3905		Serial No.: 09/519,408	
				Applicant: Takao NAKAMURA et al.			
				U.S. Filing Date: March 3, 2000 CPA FILED: 03/18/02		Art Unit: 2811	
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*EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	Cl.	Sub- Cl.	Fil. Date
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